

This Page Is Inserted by IFW Operations  
and is not a part of the Official Record

## **BEST AVAILABLE IMAGES**

Defective images within this document are accurate representations of the original documents submitted by the applicant.

Defects in the images may include (but are not limited to):

- BLACK BORDERS
- TEXT CUT OFF AT TOP, BOTTOM OR SIDES
- FADED TEXT
- ILLEGIBLE TEXT
- SKEWED/SLANTED IMAGES
- COLORED PHOTOS
- BLACK OR VERY BLACK AND WHITE DARK PHOTOS
- GRAY SCALE DOCUMENTS

**IMAGES ARE BEST AVAILABLE COPY.**

**As rescanning documents *will not* correct images,  
please do not report the images to the  
Image Problem Mailbox.**

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method of manufacturing a connection substrate, comprising steps of:

- forming a metal wire on a base;
- applying an insulating material onto the metal wire to form an insulation layer;
- forming another metal wire on the insulation layer, thereby connecting the metal wires which sandwich the insulation layer, through a contact hole formed in the insulation layer; and
- separating the metal wires and the insulation layer from the base upon irradiating through the base.

2. (Original) The method of manufacturing a connection substrate according to claim 1,

- wherein the step of applying an insulating material onto the metal wire, and the step of forming another metal wire, thereby connecting the metal wires are repeated at least two times.

3. (Original) The method of manufacturing of a connection substrate according to claim 1,

- wherein the base comprises glass.

4. (Withdrawn) A connection substrate which is manufactured by the method of claim 1.

5. (Currently Amended) A method of manufacturing a semiconductor device, comprising:

a step of forming a connection substrate on a base, comprising, forming a metal wire on a base, applying an insulating material onto the metal wire to form an insulation layer, and forming another metal wire on the insulation layer, thereby connecting the metal wires which sandwich the insulation layer through a contact hole formed in the insulation layer;

a step of mounting a semiconductor chip on the metal wire which is bared; and

a step of separating the connection substrate from the base upon irradiating through the base.

6. (Original) The method of manufacturing a semiconductor device of claim 5, wherein a plurality of the semiconductor chips are mounted on the connection substrate.

7. (Original) The method of manufacturing a semiconductor device of claim 5, wherein in the step of forming a connection substrate, the step of applying an insulating material onto the metal wire and the step of forming another metal wire, thereby connecting the metal wires are repeated at least two times.

8. (Original) The method of manufacturing a semiconductor device of claim 5, wherein the base comprises glass.

9. (Original) The method of manufacturing a semiconductor device of claim 5, wherein the base comprises silicon.

10. (Withdrawn) A semiconductor device manufactured by the method of claim 5.

11. (Currently Amended) A method of manufacturing a semiconductor device, comprising:

a step of forming a connection substrate on a base, comprising, forming a metal wire to be connected to an electrode formed on a semiconductor chip, on a first base, applying an insulating material onto the metal wire to form an insulation layer, and forming

another metal wire on the insulation layer, thereby connecting the metal wires which sandwich the insulation layer, through a contact hole formed in the insulation layer;

a step of disposing a second base on the connection substrate;

a step of separating the first base from the connection substrate;

a step of mounting a semiconductor chip on the metal wire that is bared; and

a step of separating the connection substrate from the second base upon irradiating through the base.

12. (Original) The method of manufacturing a semiconductor device of claim 11, wherein the second base comprises glass.

13. (Original) The method of manufacturing a semiconductor device of claim 11, wherein the second base comprises silicon.

14. (Original) The method of manufacturing a semiconductor device of claim 11, wherein a plurality of the semiconductor chips are mounted on the connection substrate.

15. (Original) The method of manufacturing a semiconductor device of claim 11, wherein in the step of forming a connection substrate the step of applying an insulating material onto the metal, and the step of forming another metal wire, thereby connecting the metal wires are repeated at least two times.

16. (Withdrawn) A semiconductor device manufactured by the method of claim 11.

17. (New) A method of manufacturing a connection substrate, comprising steps of:

forming a metal wire on a first surface of a light transmissive base, and the first surface is coated by a solvent having a separation reaction due to light;

applying an insulating material onto the metal wire to form an insulation layer;

forming another metal wire on the insulation layer, thereby connecting the metal wires which sandwich the insulation layer, through a contact hole formed in the insulation layer; and

separating the metal wires and the insulation layer from the light transmissive base upon radiating light through the light transmissive base.

18. (New) The method of manufacturing a connection substrate according to claim 17, the step of applying an insulating material onto the metal wire, and the step of forming another metal wire, thereby connecting the metal wires being repeated at least two times.

19. (New) A method of manufacturing a semiconductor device, comprising:  
a step of forming a connection substrate on a base, comprising, forming a metal wire on a first surface of a light transmissive base, and the first surface is coated by a solvent having a separation reaction due to light, applying an insulating material onto the metal wire to form an insulation layer and forming another metal wire on the insulation layer, thereby connecting the metal wires which sandwich the insulation layer through a contact hole formed in the insulation layer;

a step of mounting a semiconductor chip on the metal wire which is bared; and

a step of separating the connection substrate from the light transmissive base upon radiating light through the base.

20. (New) The method of manufacturing a semiconductor device of claim 19, a plurality of the semiconductor chips being mounted on the connection substrate.

21. (New) The method of manufacturing a semiconductor device of claim 19, in the step of forming a connection substrate, the step of applying an insulating material onto the metal wire and the step of forming another metal wire, thereby connecting the metal wires being repeated at least two times.

22. (New) A method of manufacturing a semiconductor device, comprising:  
a step of forming a connection substrate on a base, comprising, forming a metal wire to be connected to an electrode formed on a semiconductor chip, on a first surface of a first light transmissive base and the first surface is coated by a solvent having a separation reaction due to light, applying an insulating material on the metal wire to form an insulation layer, and forming another metal wire on the insulation layers, thereby connecting the metal wires which sandwich the insulation layer, through a contact hole formed in the insulation layer;

a step of disposing a second base on the connection substrate;

a step of separating the first light transmissive base from the connection substrate upon radiating light through the base;

a step of mounting a semiconductor chip on a metal wire that is bared; and

a step of separating the connection substrate from the second base.

23. (New) The method of manufacturing a semiconductor device of claim 22, the second base comprising glass.

24. (New) The method of manufacturing a semiconductor device of claim 22, the second base comprising silicon.

25. (New) The method of manufacturing a semiconductor device of claim 22, a plurality of the semiconductor chips being mounted on the connection substrate.

26. (New) The method of manufacturing a semiconductor device of claim 22, in the step of forming a connection substrate, the step of applying an insulating material onto the metal, and the step of forming another metal wire, thereby connecting the metal wires being repeated at least two times.